



**THE DATASHEET OF
ESD3V3S1B02LRHE6327XTSA1**



TVS Diode

Transient Voltage Suppressor Diodes

ESD3V3S1B Series

Ultra Low Clamping Bi-directional ESD / Transient Protection Diode

ESD3V3S1B-02LRH
ESD3V3S1B-02LS

Data Sheet

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Final

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Revision History

Page or Item	Subjects (major changes since previous revision)
Revision 1.1, 2011-11-28	
Revision 1.1; 2011-11-28	Features 1.1; Table 3-1; Table 3-3; Table 3-4

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Last Trademarks Update 2010-10-26

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1 Ultra Low Clamping Bi-directional ESD / Transient Protection Diode

1.1 Features

- ESD / transient protection of signal lines in low voltage applications according to:
 - IEC61000-4-2 (ESD): ± 30 kV (contact)
 - IEC61000-4-4 (EFT): 40 A (5/50 ns)
 - IEC61000-4-5 (surge): 8 A (8/20 μ s)
- Bi-directional, symmetrical working voltage up to $V_{RWM} = \pm 3.3$ V
- Ultra low clamping voltage $V_{CL} = 7$ V typ. @ $I_{PP} = 16$ A (TLP)
- Ultra low dynamic resistance $R_{DYN} = 0.13 \Omega$ typ.
- Smallest form factor: $0.62 \times 0.32 \times 0.31$ mm³
- Pb-free (RoHS compliant) and halogen free package



1.2 Application Examples

- Audio Line, Speaker, Headset, Microphone Protection
- Human Interface Devices (Keyboard, Touchpad, Buttons)

2 Product Description

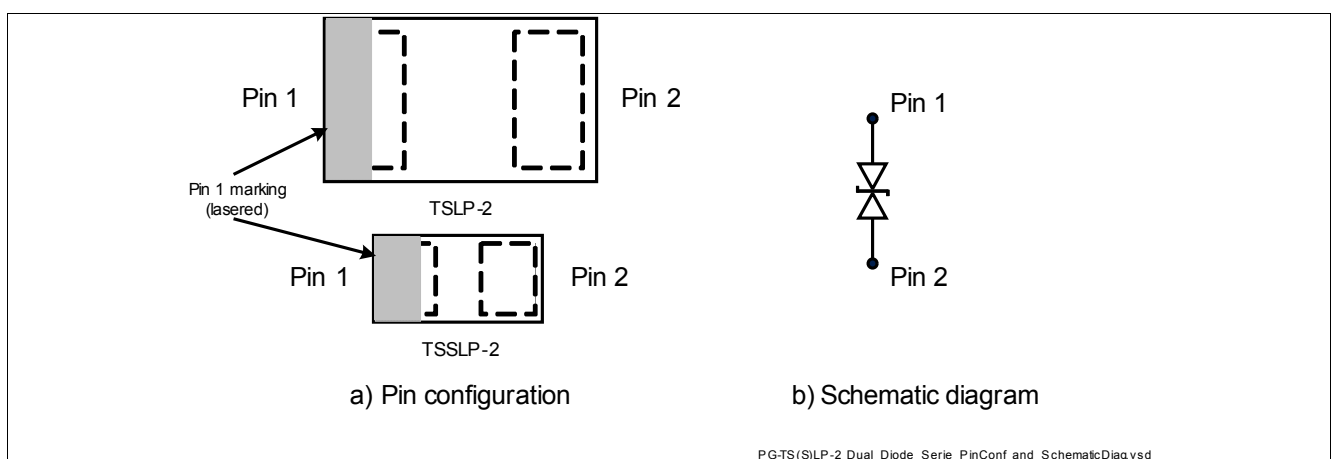


Figure 2-1 Pin Configuration and Schematic Diagram

Table 2-1 Ordering Information

Type	Package	Configuration	Marking code
ESD3V3S1B-02LRH	PG-TSLP-2-17	1 line, bi-directional	Y
ESD3V3S1B-02LS	PG-TSSLP-2-1	1 line, bi-directional	Y

3 Characteristics

Table 3-1 Maximum Ratings at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
ESD contact discharge ¹⁾	V_{ESD}	–	–	30	kV
Peak pulse current ($t_p = 8/20\ \mu\text{s}$) ²⁾	I_{PP}	–	–	8	A
Operating temperature range	T_{OP}	-40	–	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-65	–	150	$^\circ\text{C}$

1) V_{ESD} according to IEC61000-4-2

2) I_{PP} according to IEC61000-4-5

3.1 Electrical Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

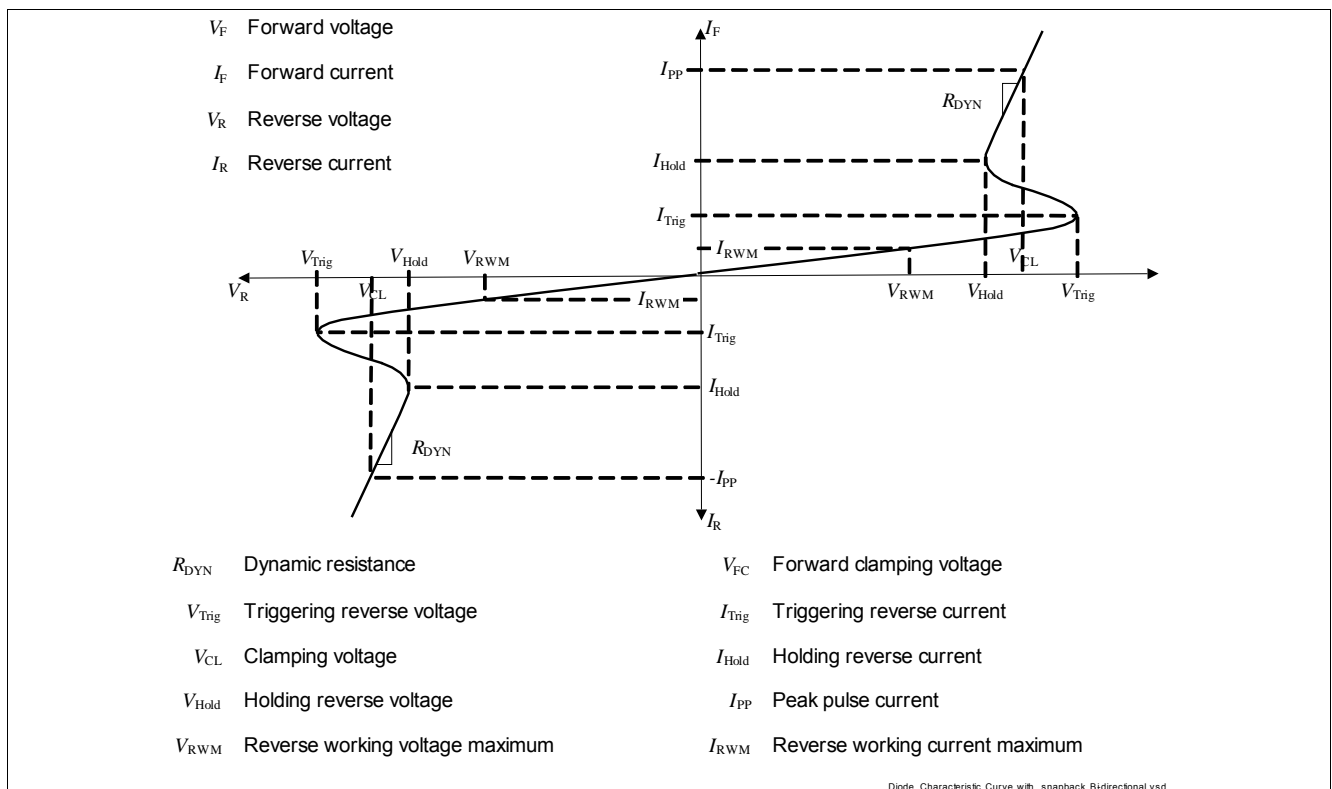


Figure 3-1 Definitions of electrical characteristics

Table 3-2 DC Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Reverse working voltage	V_{RWM}	-3.3	–	3.3	V	
Reverse current	I_R	–	–	50	nA	$V_R = 3.3\text{ V}$

Table 3-3 RF Characteristics at $T_A = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Line capacitance	C_L	–	14	20	pF	$V_R = 0\text{ V}, f = 1\text{ MHz}$

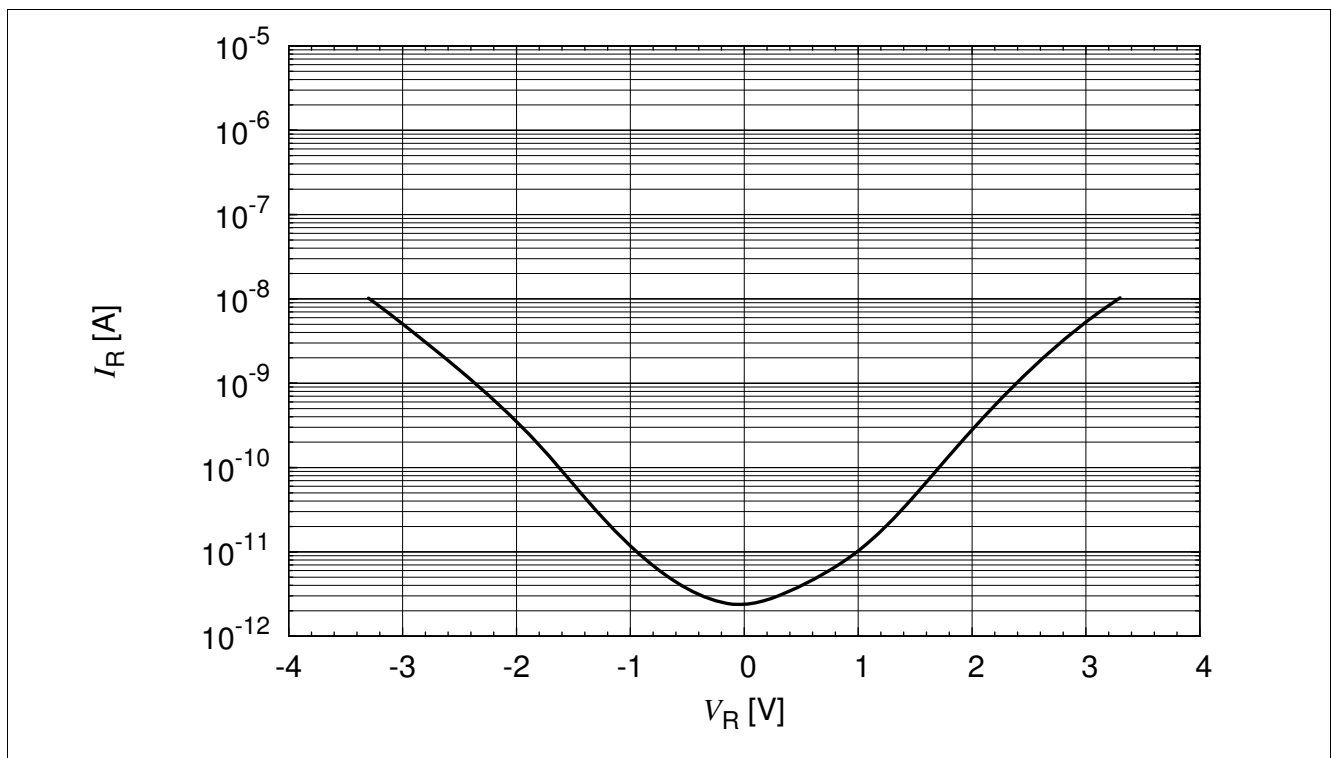
Table 3-4 ESD Characteristics at $T_A = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Clamping voltage ¹⁾	V_{CL}	–	7	–	V	$I_{PP} = 16\text{ A}, t_p = 100\text{ ns}$
		–	9	–	V	$I_{PP} = 30\text{ A}, t_p = 100\text{ ns}$
Clamping voltage ²⁾	V_{CL}	–	4.5	–	V	$I_{PP} = 1\text{ A}, t_p = 8/20\text{ }\mu\text{s}$
		–	6.8	–	V	$I_{PP} = 8\text{ A}, t_p = 8/20\text{ }\mu\text{s}$
Dynamic resistance ¹⁾	R_{DYN}	–	0.13	–	Ω	

1) Please refer to Application Note AN210 [1]. TLP parameter: $Z_0 = 50\text{ }\Omega$, $t_p = 100\text{ ns}$, $t_r = 300\text{ ps}$, averaging window: $t_1 = 30\text{ ns}$ to $t_2 = 60\text{ ns}$, extraction of dynamic resistance using least squares fit of TLP characteristics between $I_{PP1} = 10\text{ A}$ and $I_{PP2} = 40\text{ A}$.

2) I_{PP} according to IEC61000-4-5

3.2 Typical Characteristics at $T_A = 25\text{ °C}$, unless otherwise specified


Figure 3-2 Reverse current: $I_R = f(V_R)$

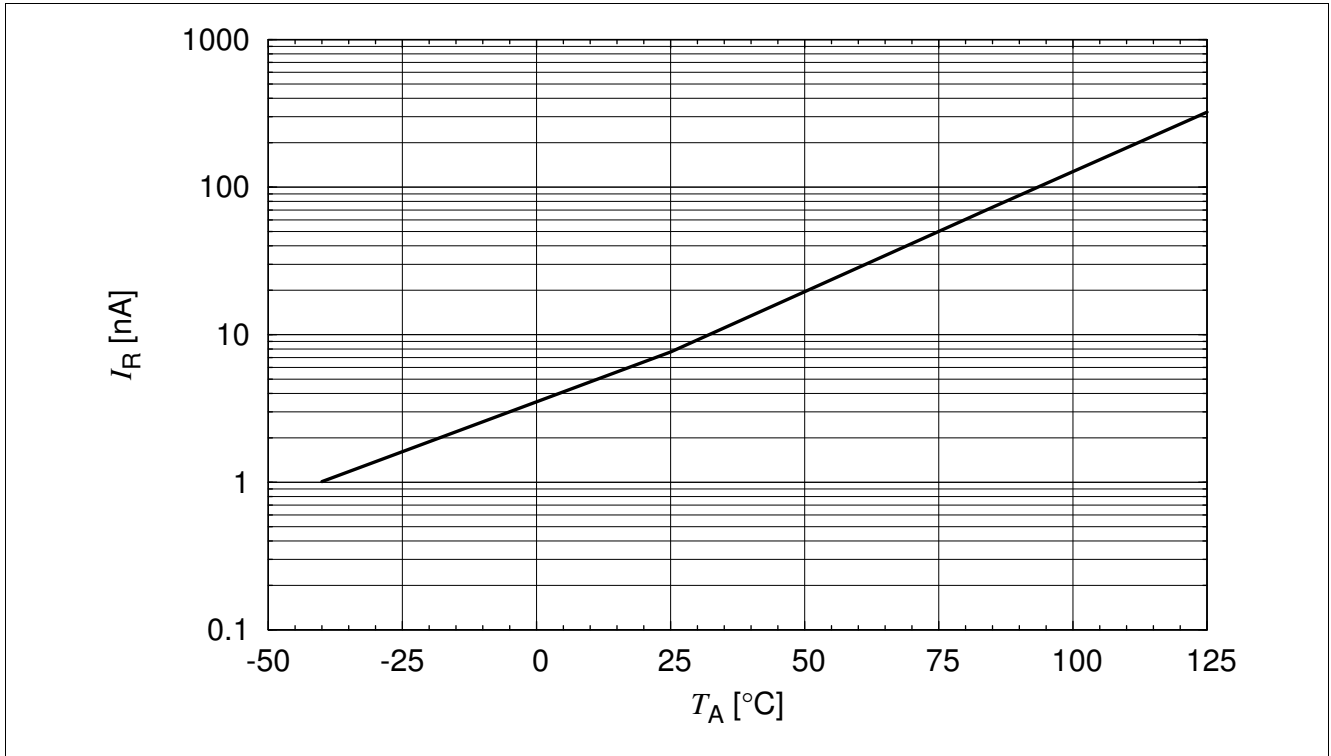


Figure 3-3 Reverse current: $I_R = f(T_A)$, $V_R = 3.3 V$

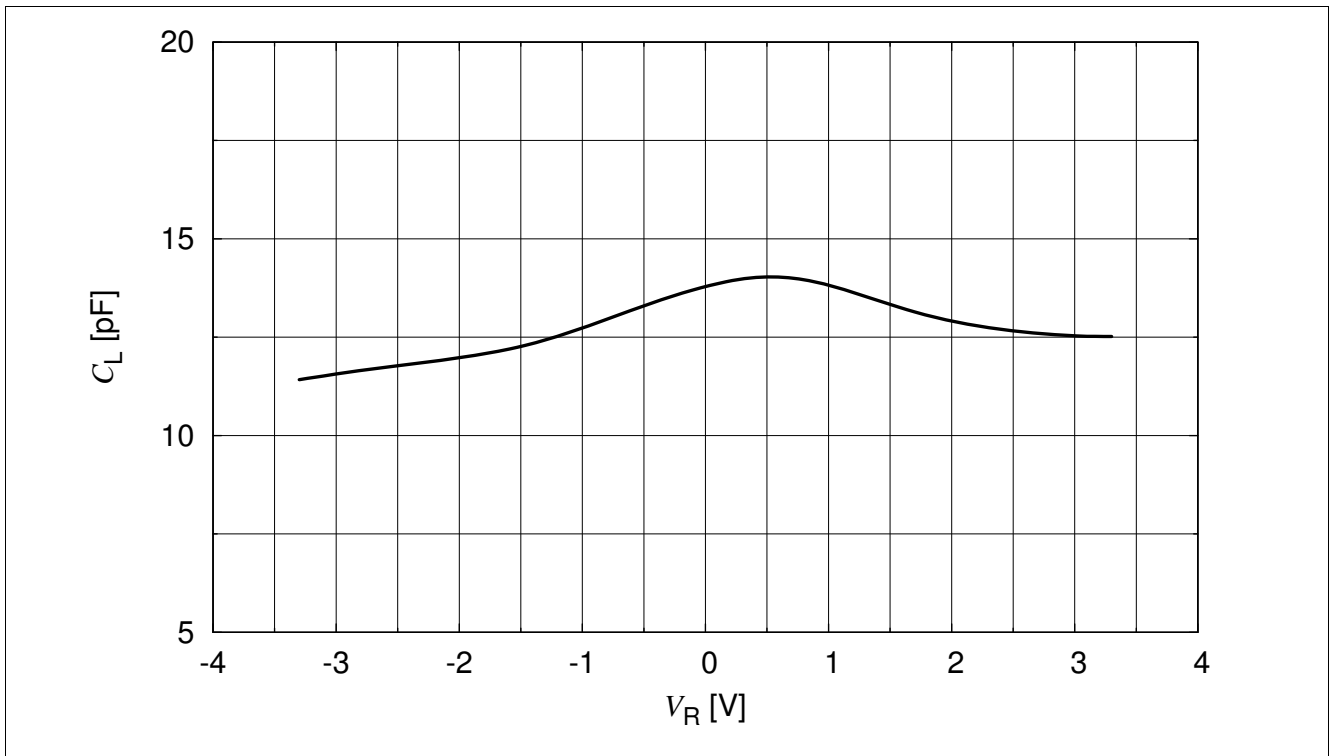


Figure 3-4 Line capacitance: $C_L = f(V_R)$, $f = 1 MHz$

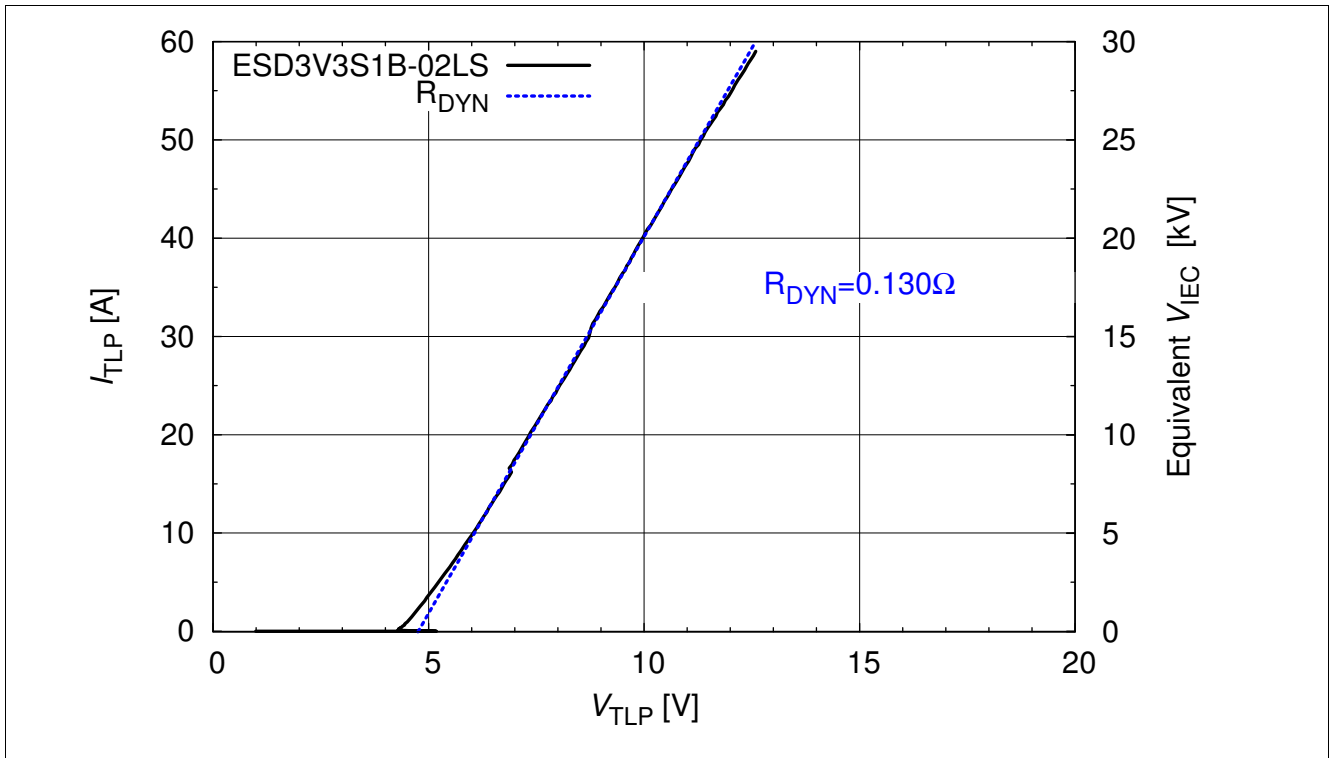


Figure 3-5 Clamping voltage (TLP): $I_{TLP} = f(V_{TLP})$, from pin 1 to pin 2 [1]

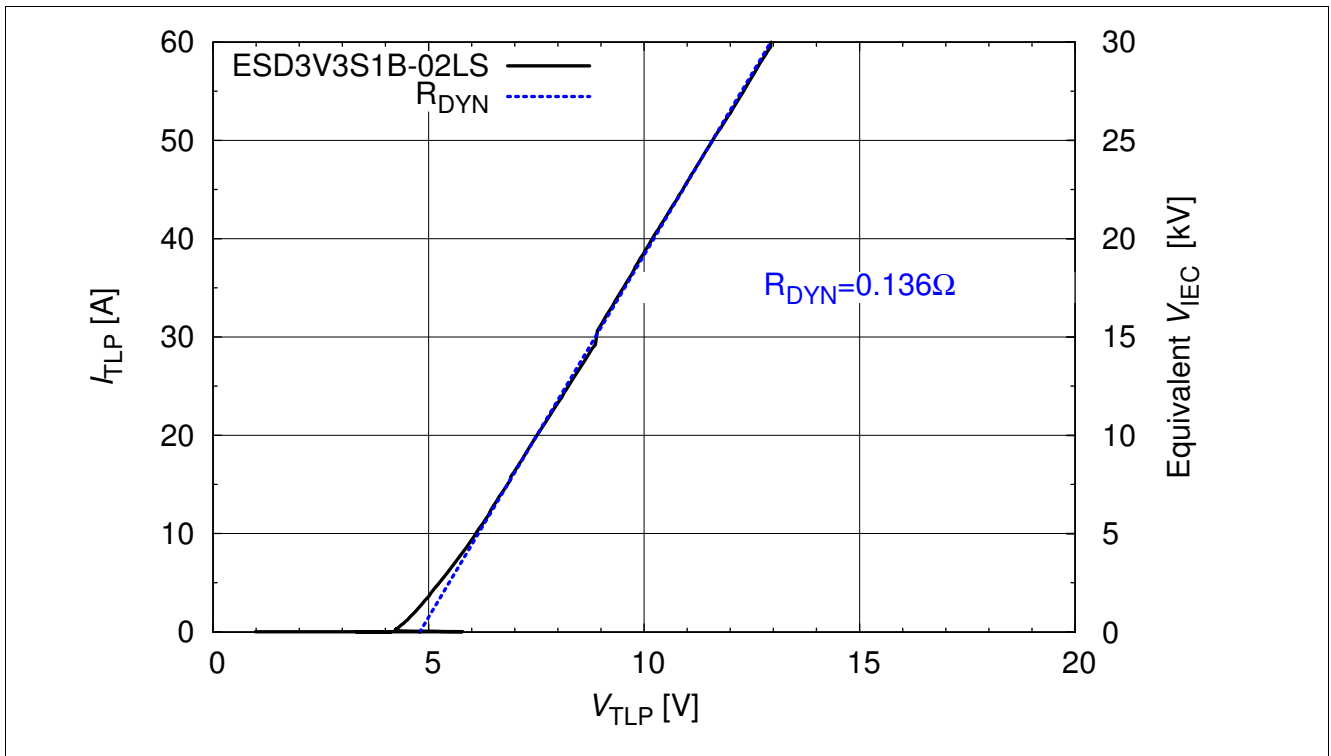


Figure 3-6 Clamping voltage (TLP): $I_{TLP} = f(V_{TLP})$, from pin 2 to pin 1 [1]

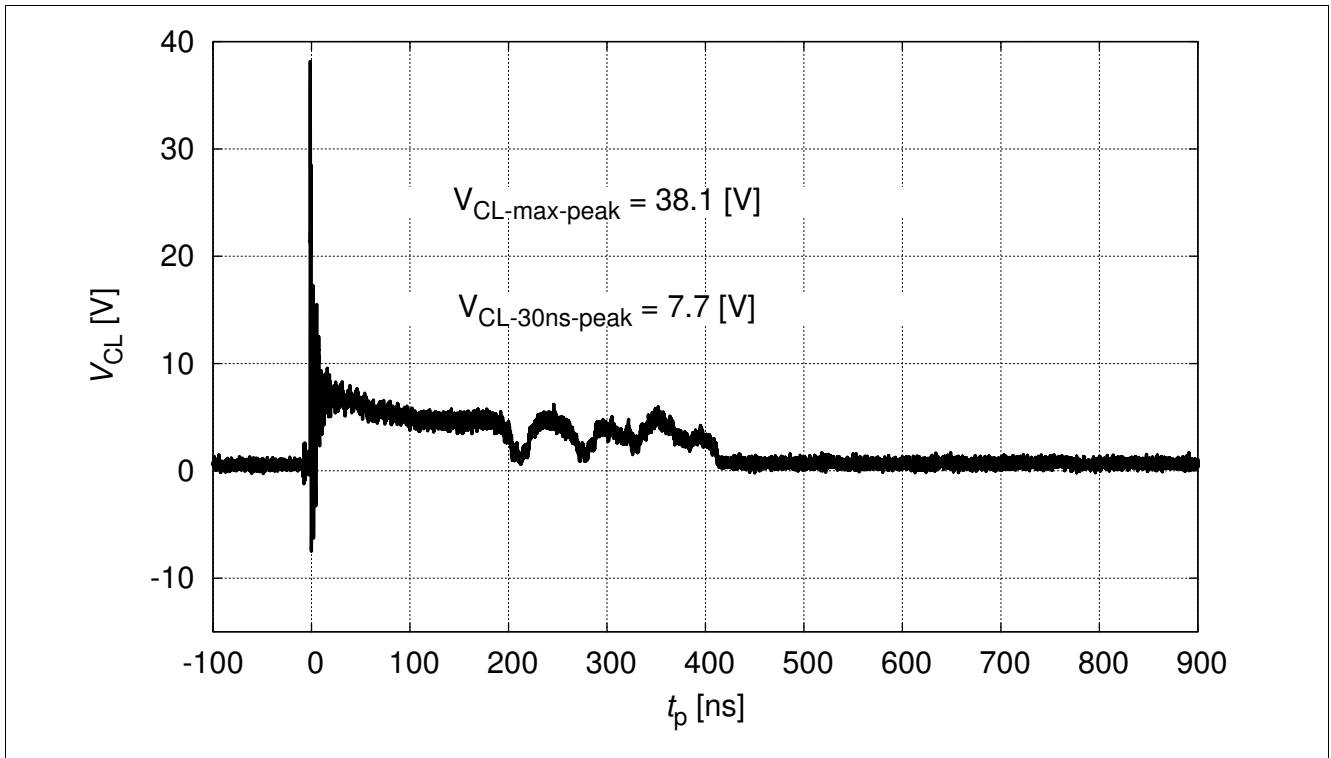


Figure 3-7 IEC61000-4-2 : $V_{CL} = f(t)$, 8 kV positive pulse from pin 1 to pin 2

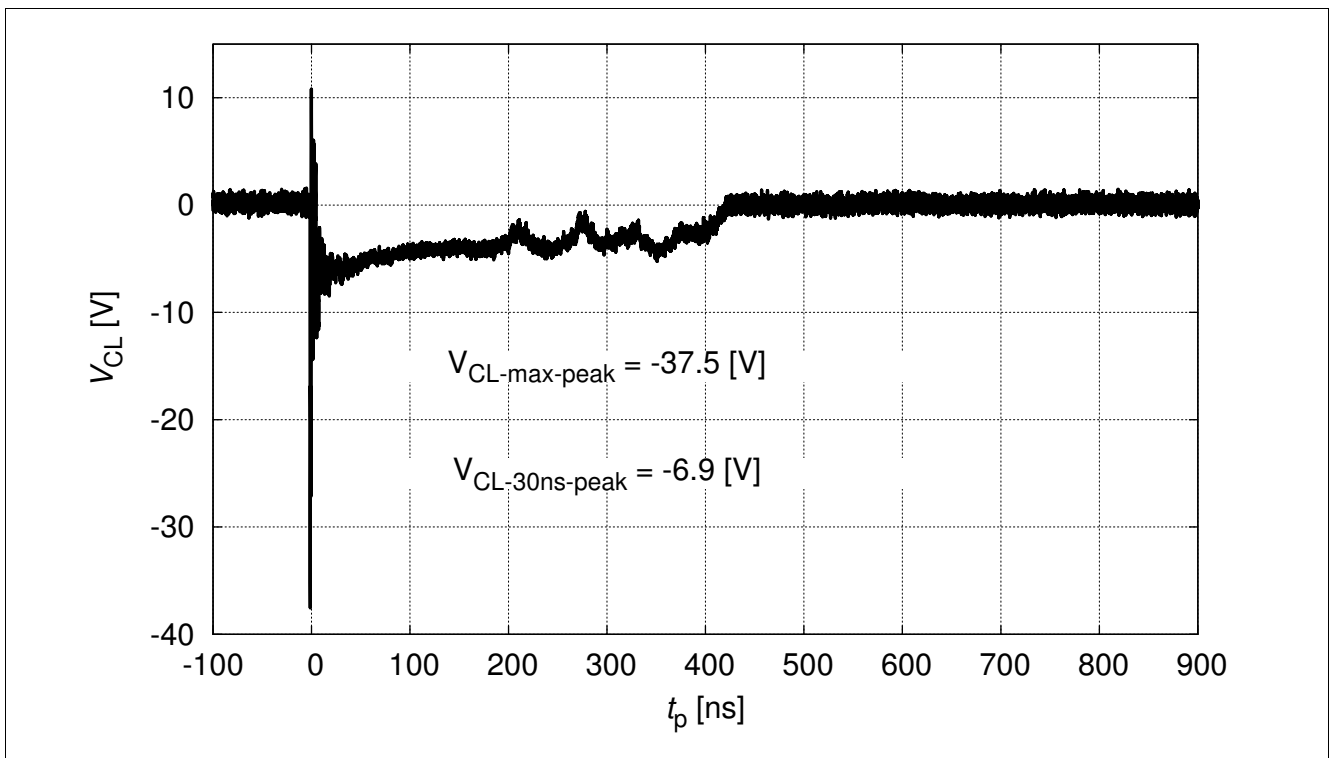


Figure 3-8 IEC61000-4-2 : $V_{CL} = f(t)$, 8 kV negative pulse from pin 1 to pin 2

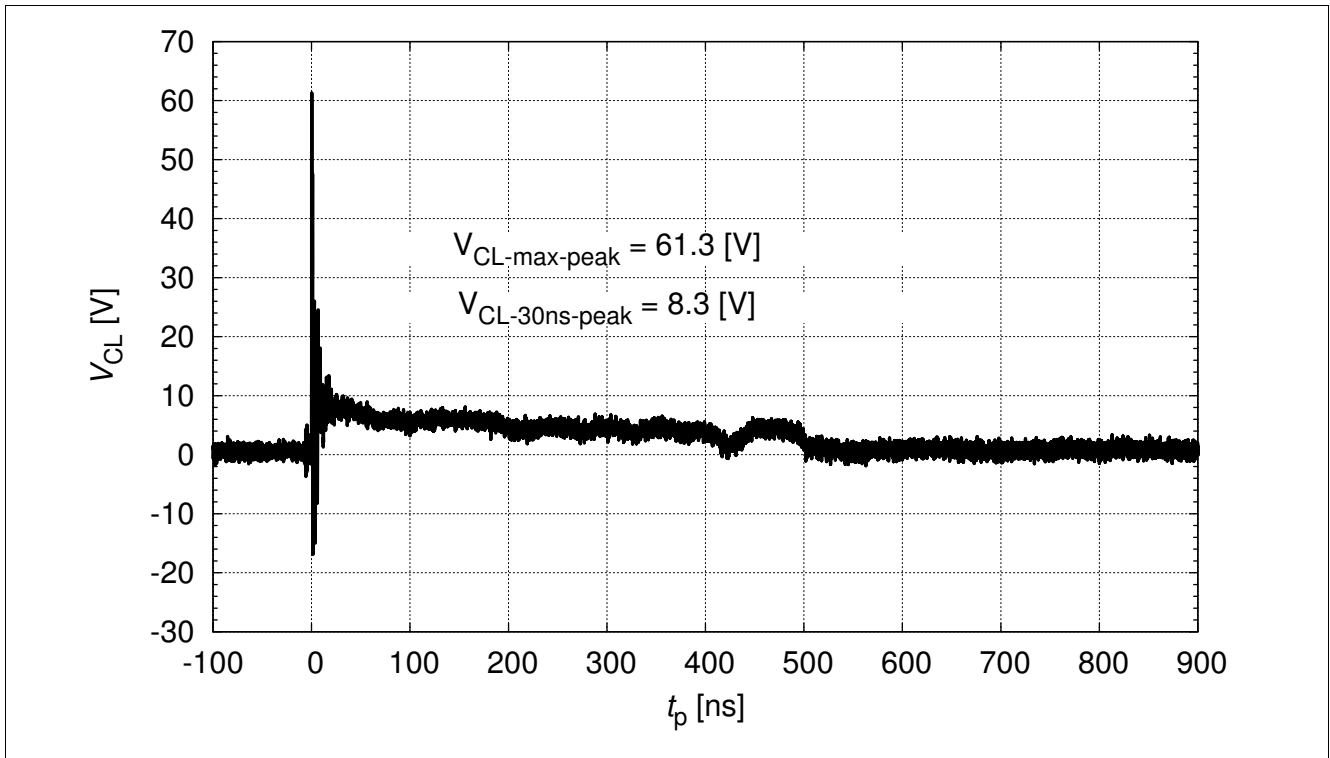


Figure 3-9 IEC61000-4-2 : $V_{CL} = f(t)$, 15 kV positive pulse from pin 1 to pin 2

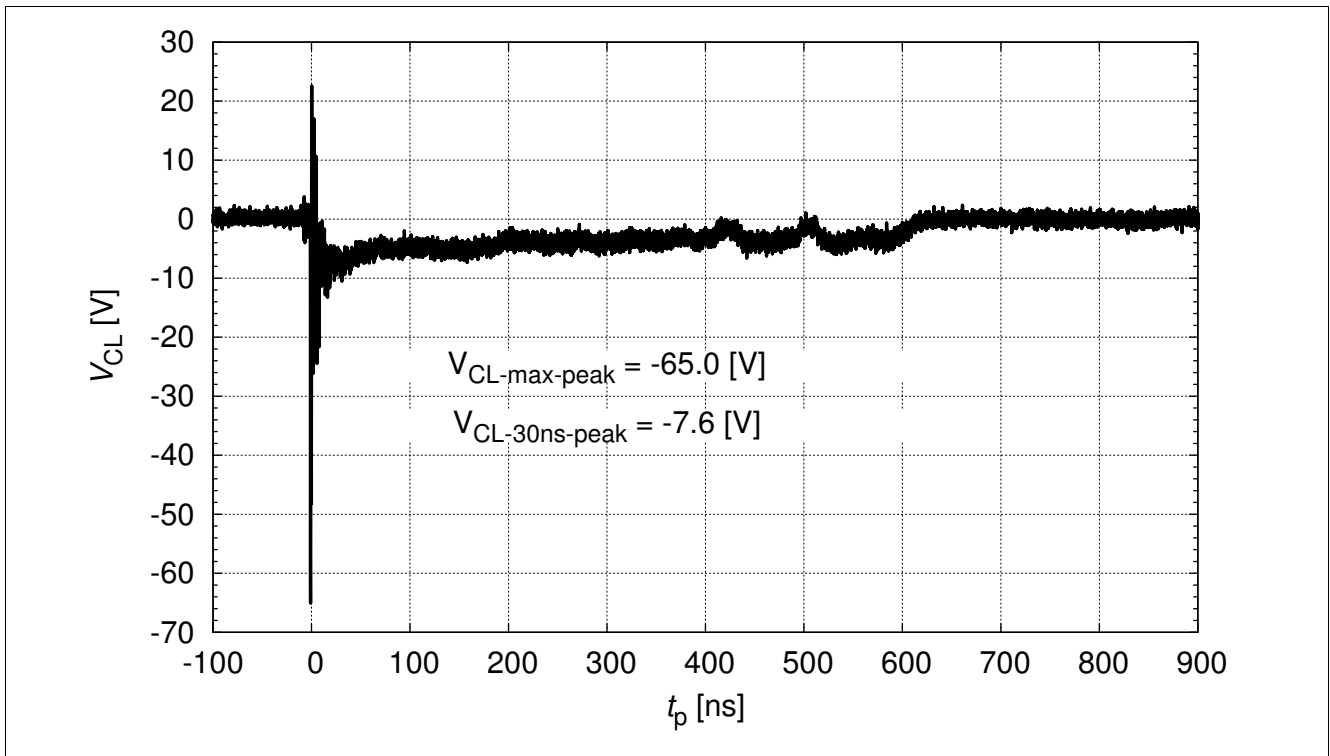


Figure 3-10 IEC61000-4-2 : $V_{CL} = f(t)$, 15 kV negative pulse from pin 1 to pin 2

4 Application Information

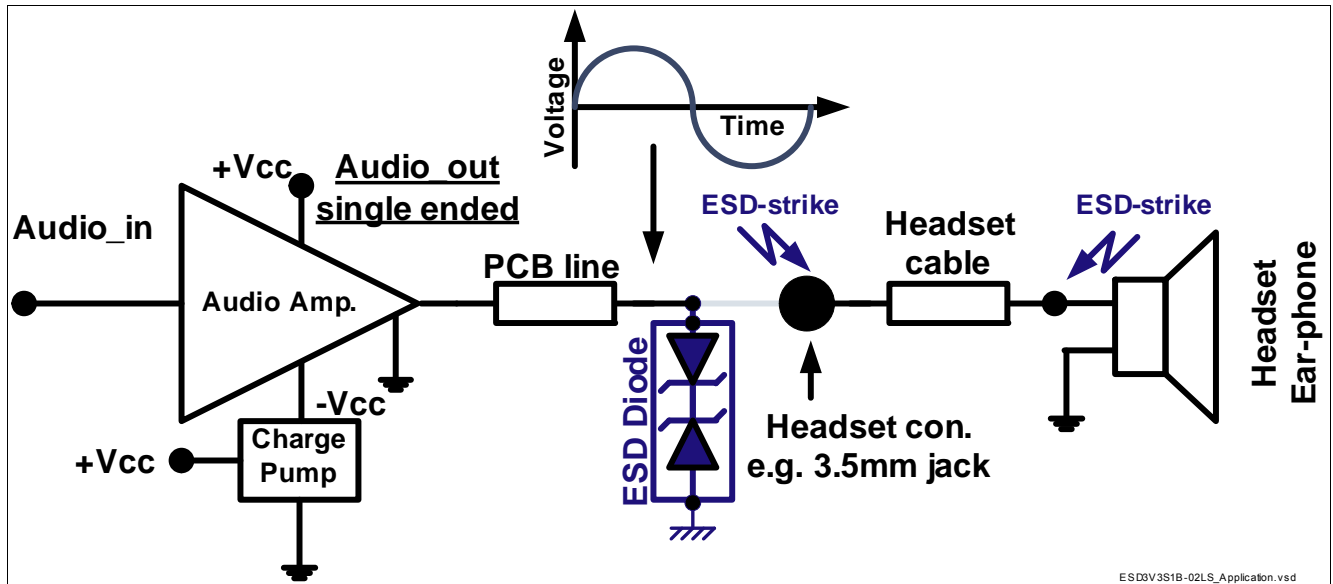


Figure 4-1 Single line, bi-directional ESD / Transient protection

5 Ordering Information Scheme (Examples)

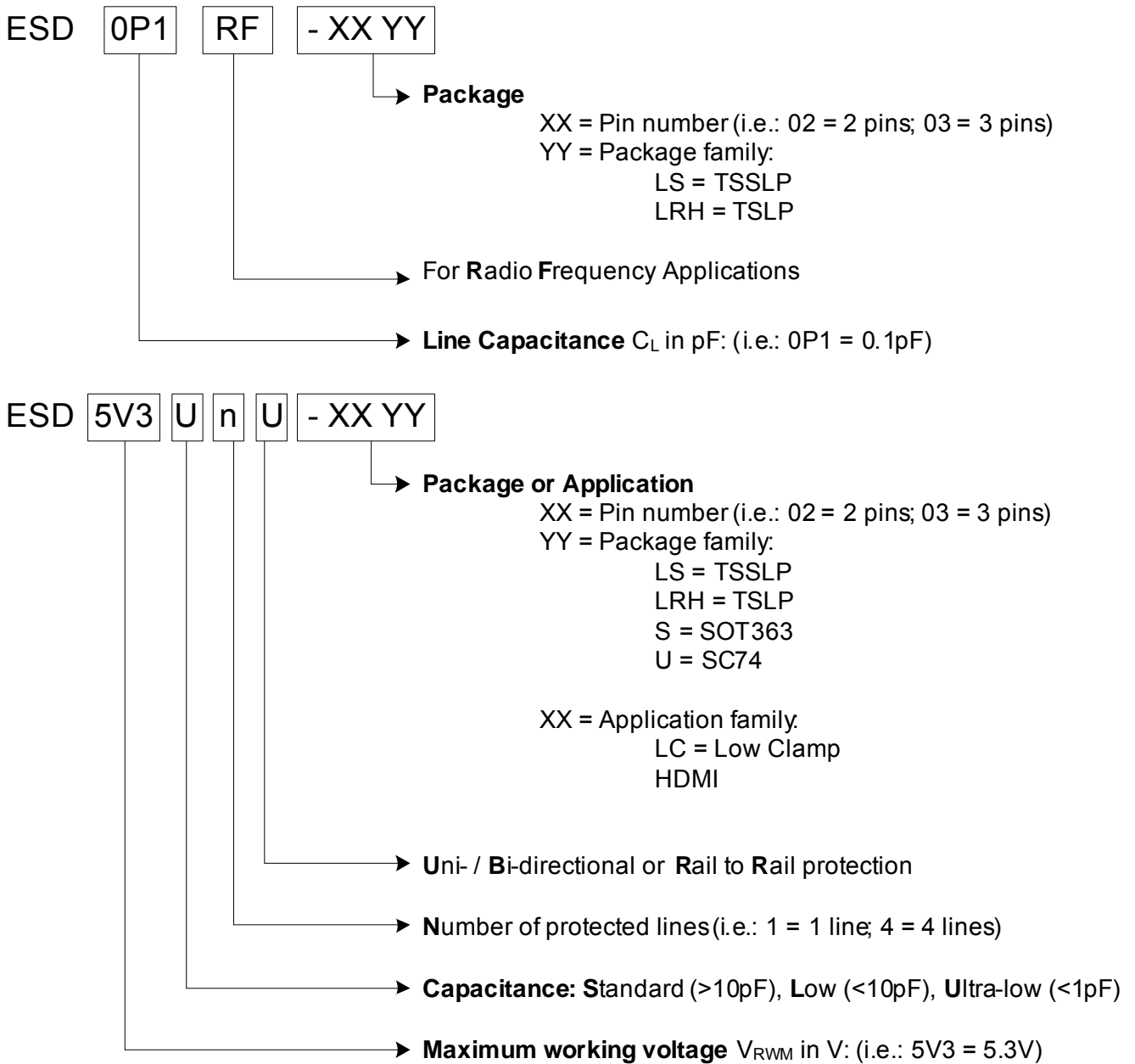


Figure 5-1 Ordering information scheme

6 Package Information

6.1 PG-TSLP-2-17 (mm) [2]

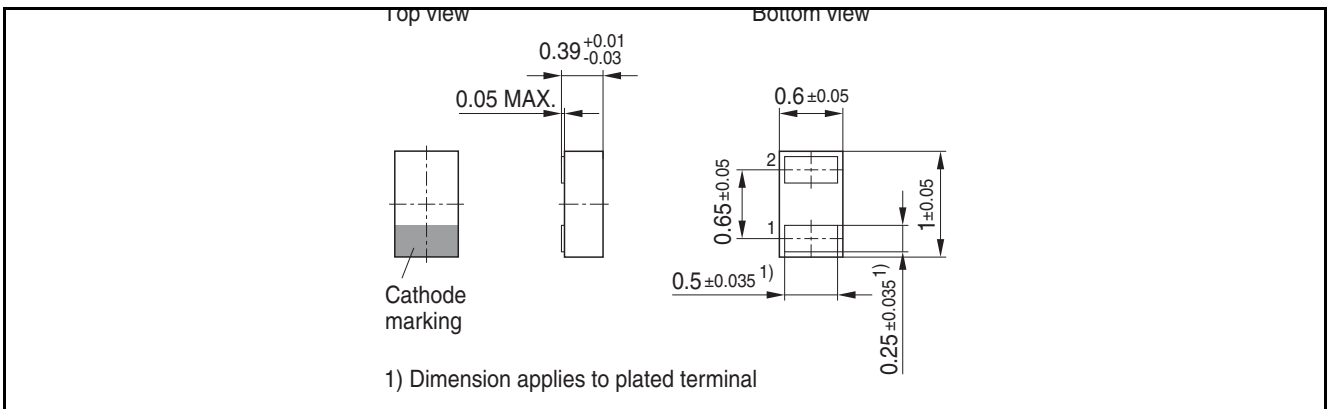


Figure 6-1 PG-TSLP-2-17: Package overview

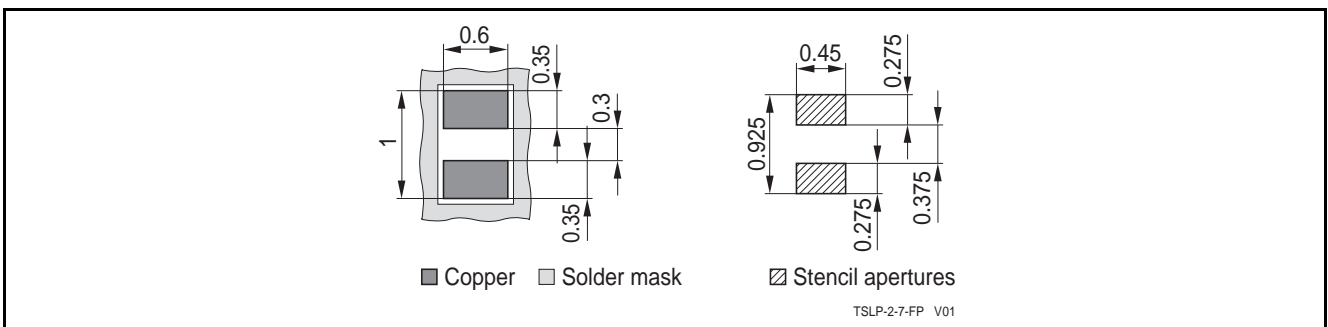


Figure 6-2 PG-TSLP-2-17: Footprint

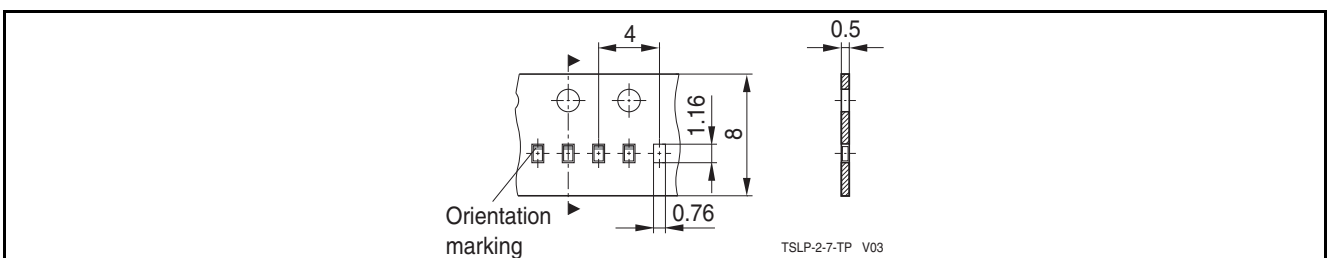


Figure 6-3 PG-TSLP-2-17: Packing

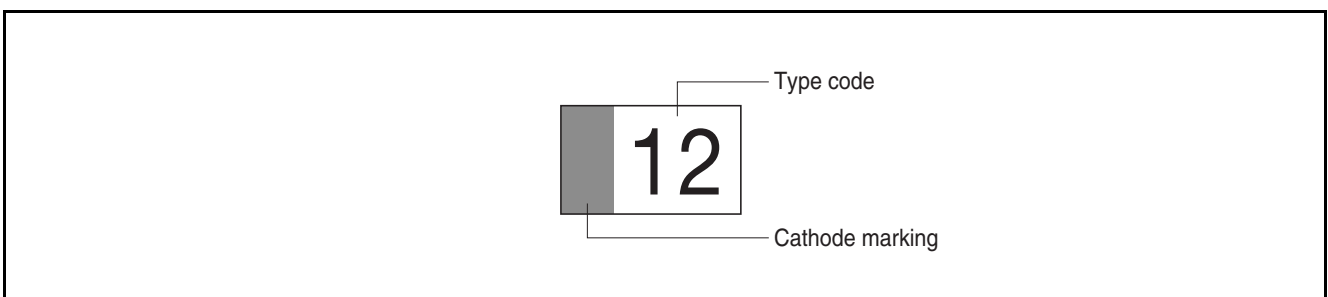


Figure 6-4 PG-TSLP-2-17: Marking (example)

6.2 PG-TSSLP-2-1 (mm) [2]

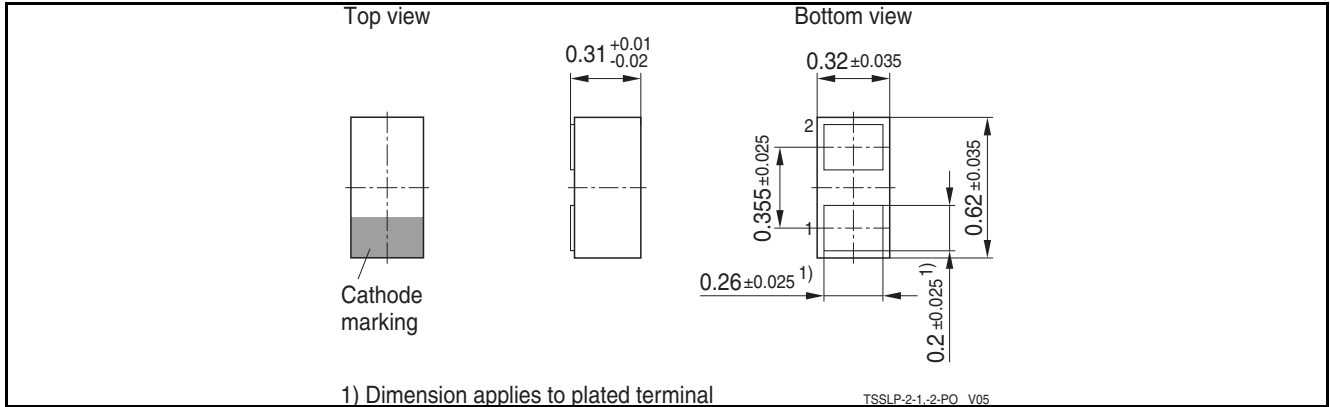


Figure 6-5 PG-TSSLP-2-1: Package overview

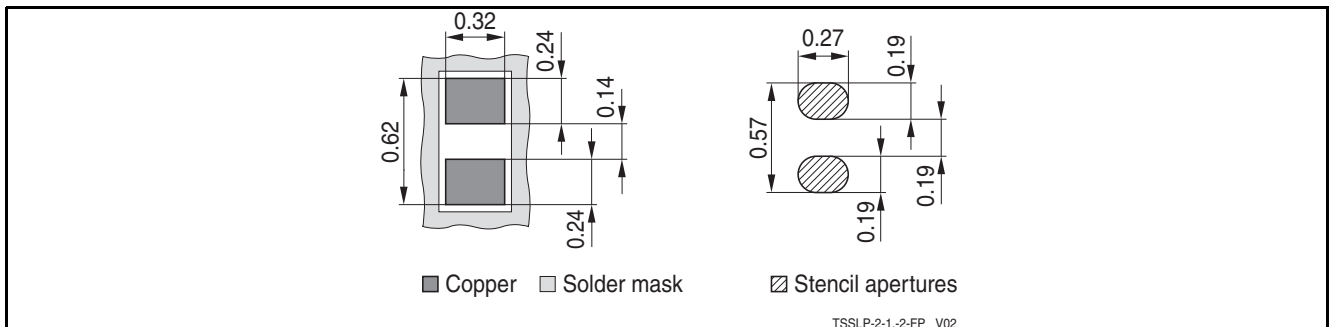


Figure 6-6 PG-TSSLP-2-1: Footprint

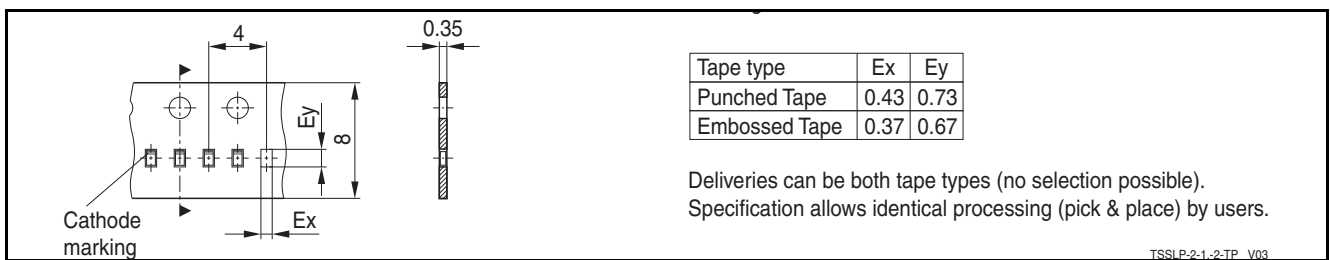


Figure 6-7 PG-TSSLP-2-1: Packing

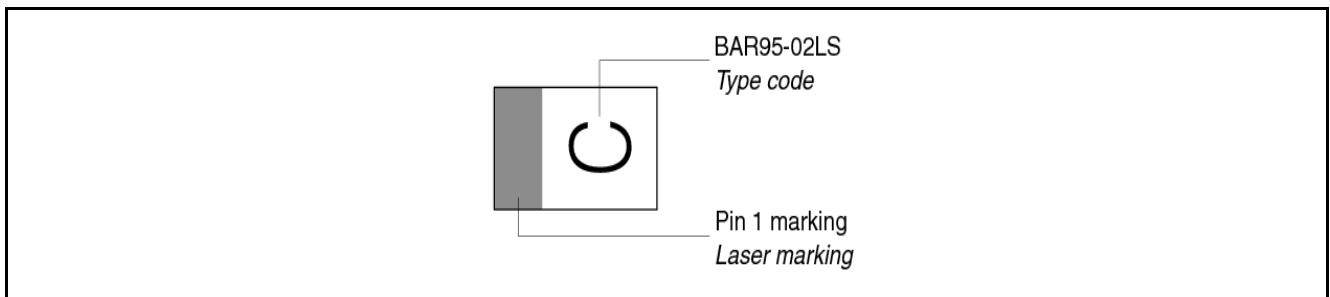


Figure 6-8 PG-TSSLP-2-1: Marking (example)

References

- [1] Infineon AG - **Application Note AN210**: Effective ESD Protection design at System Level Using VF-TLP Characterization Methodology
- [2] Infineon AG - Recommendations for PCB Assembly of Infineon TSLP and TSSLP Packages

Terminology

C_L	Line capacitance
EFT	Electrical Fast Transient
ESD	Electrostatic Discharge
I_{PP}	Peak pulse current
I_R	Reverse current
LCD	Liquid Crystal Display
P_{PK}	Peak pulse power
R_{DYN}	Dynamic resistance
RoHs	Restriction of Hazardous Substance directive
T_A	Ambient temperature
T_{OP}	Operation temperature
t_p	Pulse duration
T_{stg}	Storage temperature
V_{BR}	Breakdown voltage
V_{CL}	Reverse clamping voltage
V_{ESD}	Electrostatic discharge voltage
V_R	Reverse voltage
V_{RWM}	Reverse working voltage maximum

Predefined Names

Name	Initial Cross-Reference
X-GOLD	X-GOLD
XMM	XMM

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Frequently used expressions, such as component names, file names, tools releases, version numbers, proprietary variables and software links, can be used in a similar way as user variables. However, they must be listed in a special table and **not** in the standard file “Variables”.

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2. New definitions must be inserted in a new row. Never change existing definitions, as they might be used in other documents.
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